Unit in mm

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2SA1297

POWER AMPLIFIER APPLICATIONS

POWER SWITCHING APPLICATIONS

- Low Saturation Voltage : $V_{CE (sat)} = -0.5V (Max.) @I_{C} = -2A$
- Complementary to 2SC3267.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	v_{CBO}	-20	V
Collector-Emitter Voltage	v_{CEO}	-20	V
Emitter-Base Voltage	v_{EBO}	6	V
Collector Current	$I_{\mathbf{C}}$	-2	A
Base Current	I_{B}	-0.5	Α
Collector Power Dissipation	$P_{\mathbf{C}}$	400	mW
Junction Temperature	T_{j}	150	$^{\circ}\mathrm{C}$
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~150	$^{\circ}\mathrm{C}$

1. EMITTER 2. COLLECTOR 3. BASE JEDEC EIAJ TOSHIBA 2-4E1A

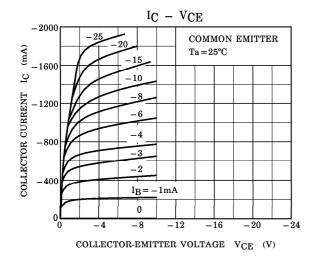
Weight: 0.13g

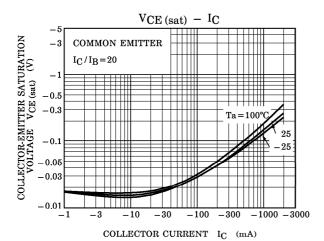
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

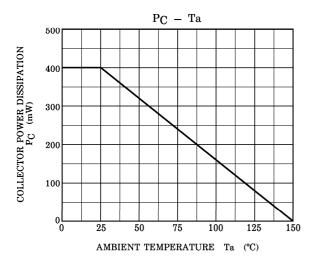
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -20V, I_E = 0$	_		-0.1	μ A
Emitter Cut-off Current	$I_{ m EBO}$	$V_{EB} = -6V, I_C = 0$	_	_	-0.1	μ A
Collector-Emitter Breakdown Voltage	V (BR) CEO	$I_{C} = -10 \text{mA}, I_{B} = 0$	-20	_	_	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	$I_{E} = -0.1 \text{mA}, I_{C} = 0$	-6	_	_	V
DC Current Gain	hFE (1) (Note)	$V_{CE} = -2V, I_{C} = -0.1A$	120	_	400	
	h _{FE} (2)	$V_{CE} = -2V, I_{C} = -2A$	40		_	
Collector-Emitter Saturation Voltage	V _{CE} (sat)	$I_{C} = -2A, I_{B} = -0.1A$	_	_	-0.5	V
Base-Emitter Voltage	$v_{ m BE}$	$V_{CE} = -2V, I_{C} = -0.1A$	_	_	-0.85	V
Transition Frequency	$\mathbf{f_T}$	$V_{CE} = -2V, I_{C} = -0.5A$	_	120		MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		40	_	рF

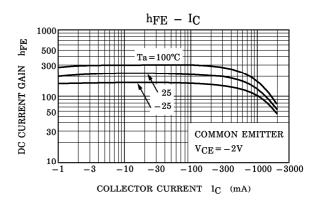
Note: $h_{FE(1)}$ Y: 120~240, GR: 200~400

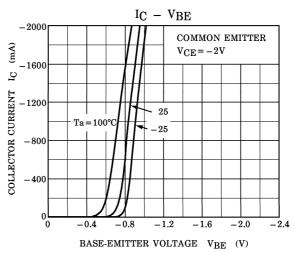
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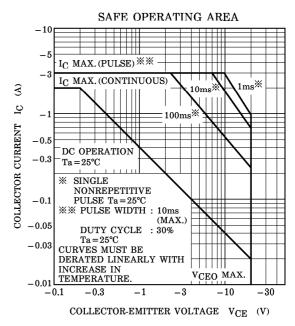












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